Characteristics ESDA6V1S3

1 Characteristics

Table 1. Absolute ratings ($T_{amb} = 25$ °C)

Symbol	Р	Value	Unit	
V _{PP}	Peak pulse voltage Electrostatics discharge: MIL STD 883C-Method 3015-6		25	kV
P _{PP}	Peak pulse power (8/20µs)	200	W	
T _j	Maximum operating junction temp	+150	°C	
T _{stg}	Storage temperature range	-55 to +150	°C	
T _L	Maximum lead temperature for so	260	°C	

Figure 2. Electrical characteristics (definitions)

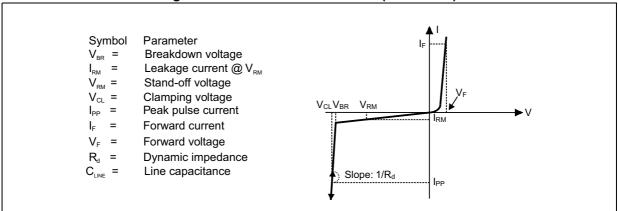


Table 2. Electrical characteristics - values (T_{amb} = 25 °C)

	V _{BR} at I _R		I _{RM} at V _{RM}		V _F at I _F		α T⁽¹⁾	C _{line} at 0 V	
Types	min.	max.		max. ⁽²⁾		max.		max.	typ.
	٧	V	mA	μΑ	V	٧	mA	10 ⁻⁴ /C	pF
ESDA6V1S3	6.1	7.2	1	2	5.25	1.25	200	6	120

- 1. $\Delta V_{BR} = \alpha T^* (T_{amb} 25 \, ^{\circ}C) \, ^{*}V_{BR} (25 \, ^{\circ}C)$
- 2. Between any I/O pin and ground.

2 Calculation of the clamping voltage

2.1 Use of the dynamic resistance

The ESDA family has been designed to clamp fast spikes like ESD. Generally the PCB designers need to calculate easily the clamping voltage V_{CL} . This is why we give the dynamic resistance in addition to the classical parameters. The voltage across the protection cell can be calculated with the following formula:

$$V_{CL} = V_{BR} + Rd I_{PP}$$

Where Ipp is the peak current through the ESDA cell.

2.2 Dynamic resistance measurement

The short duration of the ESD has led us to prefer a more adapted test wave, as below defined, to the classical $8/20 \mu s$ and $10/1000 \mu s$ surges.

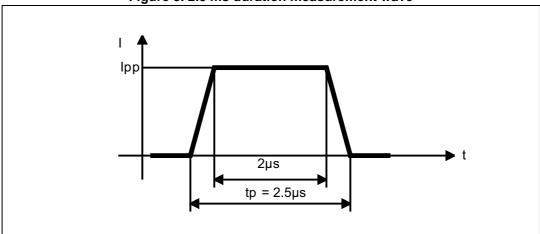


Figure 3. 2.5 ms duration measurement wave

As the value of the dynamic resistance remains stable for a surge duration lower than 20 μs , the 2.5 μs rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

Figure 4. Peak power dissipation versus initial junction temperature (T_i initial = 25 °C)

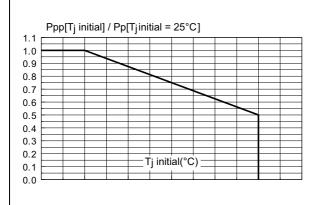


Figure 5. Peak pulse power versus exponential pulse duration (T_i initial = 25 °C)

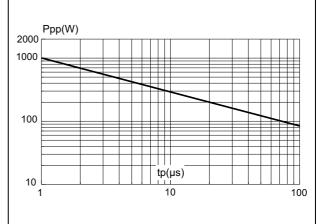


Figure 6. Clamping voltage versus peak pulse current (T_i initial = 25 °C), rectangular waveform

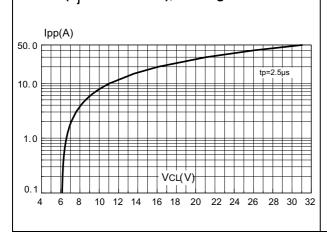


Figure 7. Capacitance versus reverse applied voltage (typical values)

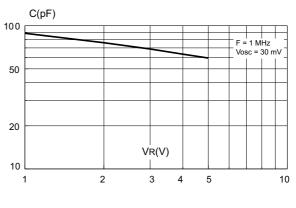


Figure 8. Relative variation of leakage current versus junction temperature (typical values)

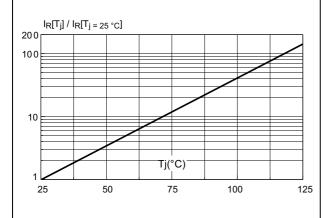
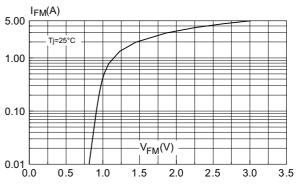


Figure 9. Peak forward voltage drop versus peak forward current (typical values)

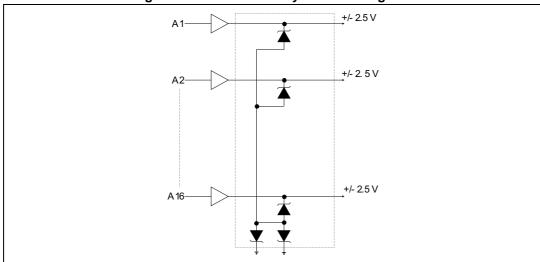


57

3 Application example

Figure 10. Protection of logic-level signals (ex: centronics junction)

Figure 11. Protection of symmetrical signals



Note: Capacitance value between any I/O pin and ground is divided by 2.

Implementing its ASD™ technology, STMicroelectronics has developed a monolithic Transil™ diode array, which is a reliable protection against electrostatic overloads for computer I/O ports, modems, GSM handsets and accessories or other similar systems with data outputs. The ESDA6V1S3 integrates 18 Transil™ diodes in a compact package that can be easily mounted close to the circuitry to be protected, eliminating the assembly costs associated with the use of discrete diodes, and also increasing system reliability.

Each Transil[™] has a breakdown voltage between 6.2 V (minimum) and 7.2 V (maximum). When the input voltage is lower than the breakdown voltage, the diodes present a high impedance to ground. For short overvoltage pulses, the fast-acting diodes provide an almost instantaneous response, clamping the voltage to a safe level.

Package information ESDA6V1S3

Package information 4

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

SO-20 package information 4.1

D

Figure 12. SO-20 package outline

Table 3. SO-20 package mechanical data

	Dimensions							
Ref.		Millimeters		Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	2.35		2.65	0.092		0.104		
A1	0.10		0.20	0.004		0.008		
В	0.33		0.51	0.013		0.020		
С	0.23		0.32	0.009		0.013		
D	12.6		13.0	0.484		0.512		
E	7.40		7.60	0.291		0.299		
е		1.27			0.050			
Н	10.0		10.65	0.394		0.419		
h	0.25		0.75	0.010		0.029		
L	0.50		1.27	0.020		0.050		
K			8°			8°		



6/8 DocID5480 Rev 5

5 Ordering information

Figure 13. Ordering information scheme

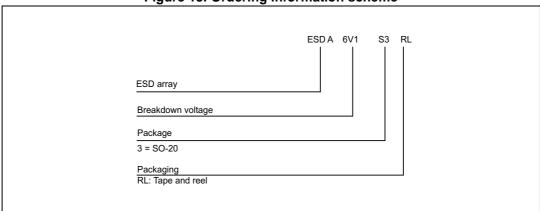


Table 4. Ordering information

Order codes	Marking	Package	Weight	Base qty	Delivery mode
ESDA6V1S3	E6V1S3	SO-20	0.55 g	1000	Tape and reel

6 Revision history

Table 5. Document revision history

Date	Revision	Changes
18-Sep-2014	4	
13-Nov-2015	5	Removed ESDA6V2S6 package information.

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